

ABSTRACT OF THE DISCLOSURE

A method for manufacturing a semiconductor device wherein a cylindrical capacitor is formed by selectively etching an oxide film in a cell area for preventing bridging between cells during a wet etching process of the oxide film in the cell area
5 is described herein. A step difference between the interlayer insulating film formed in the cell area and the interlayer insulating film formed in the peripheral circuit area is minimized by covering the peripheral circuit area by the photoresist film and selectively etching the oxide film in the cell area to form a cylindrical capacitor, thereby simplifying the manufacturing process. In addition, bridging between the
10 cells is prevented by performing a simple wet etching process using a single wet station, without performing a separate dry etching process for removing the oxide film and the photoresist film pattern, thereby improving the yield of the device.